



Schottky Diode Gen ²

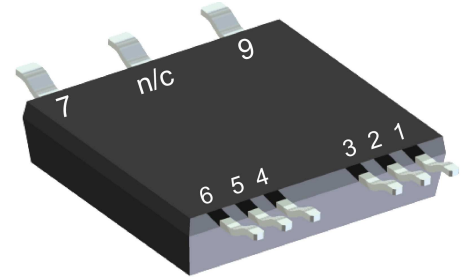
$V_{RRM} = 150\text{ V}$
 $I_{FAV} = 2 \times 75\text{ A}$
 $V_F = 0.74\text{ V}$

High Performance Schottky Diode
Low Loss and Soft Recovery
Parallel legs

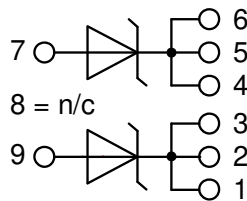
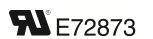
Part number

DSA120X150LB

Marking on Product: *DSA120X150LB*



Backside: isolated



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

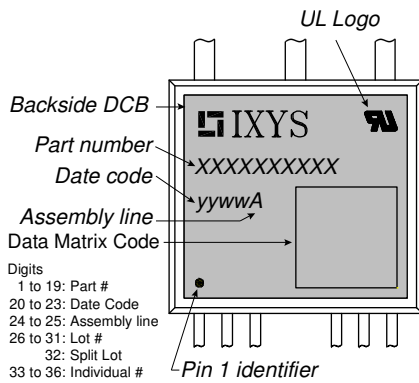
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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					150	V
V_{RRM}	max. repetitive reverse blocking voltage					150	V
I_R	reverse current, drain current	$V_R = 150\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		1	mA
		$V_R = 150\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		5	mA
V_F	forward voltage drop	$I_F = 60\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.93	V
		$I_F = 120\text{ A}$				1.13	V
		$I_F = 60\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.74	V
		$I_F = 120\text{ A}$				0.95	V
I_{FAV}	average forward current	$T_C = 135^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		75	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.51	V
r_F	slope resistance					1.3	mΩ
R_{thJC}	thermal resistance junction to case					0.8	K/W
R_{thCH}	thermal resistance case to heatsink				0.40		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		185	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		700	A
C_J	junction capacitance	$V_R = 24\text{ V}$	$f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		481	pF



Package SMPD		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				8.5		g
F_C	mounting force with clip		40		130	N
$d_{Spp/ App}$	creepage distance on surface / striking distance through air	terminal to terminal	1.6			mm
$d_{Spb/ Apb}$		terminal to backside	4.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Part description

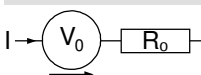
- D = Diode
- S = Schottky Diode
- A = low VF
- 120 = Current Rating [A]
- X = Parallel legs
- 150 = Reverse Voltage [V]
- LB = SMPD-B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA120X150LB-TUB	DSA120X150LB	Tube	20	524766
Alternative	DSA120X150LB-TRR	DSA120X150LB	Tape & Reel	200	517173

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175\text{ °C}$



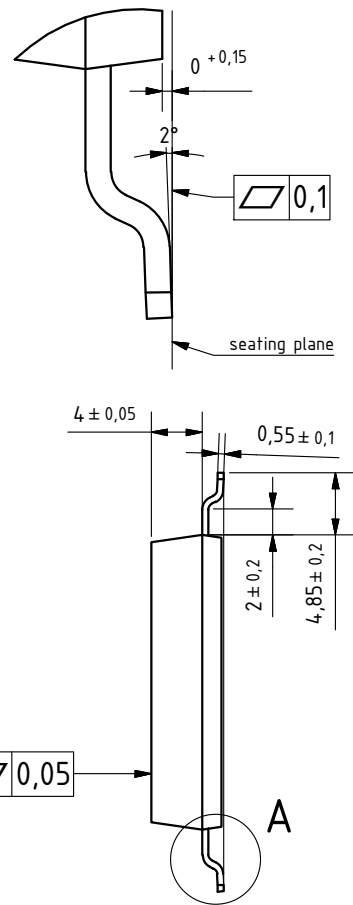
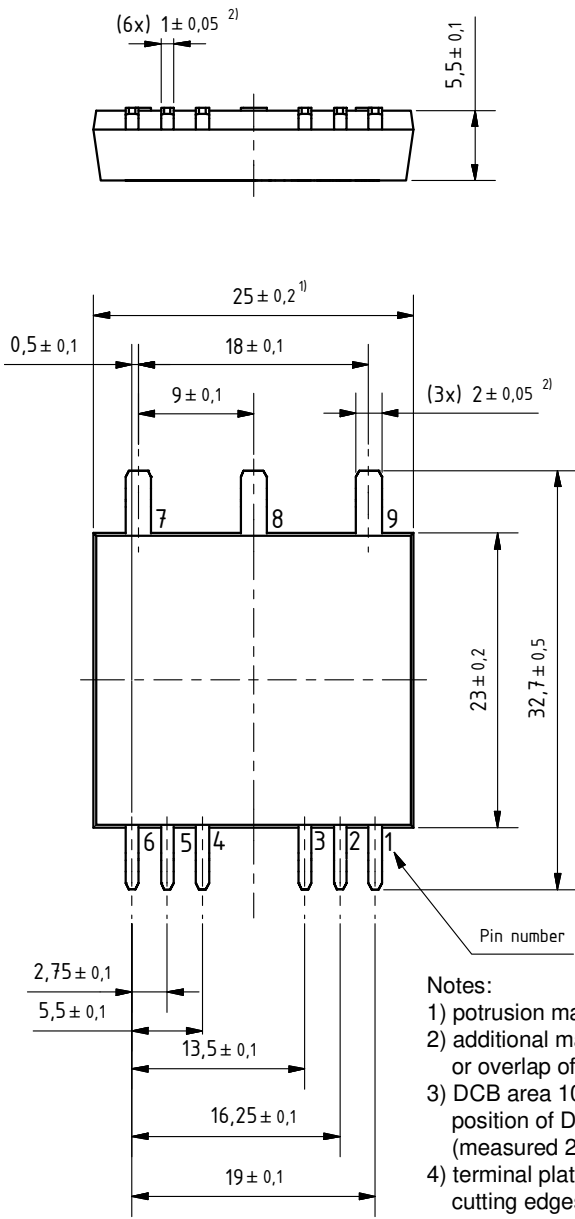
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$V_{0\ max}$	threshold voltage	0.51	V
$R_{0\ max}$	slope resistance *	1.3	mΩ



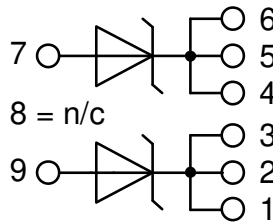
Outlines SMPD

A (8 : 1)



Notes:

- 1) protrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignment or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 μm convex; position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$ (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 - 1 μm Ni + 10 - 25 μm Sn (gal v.) cutting edges may be partially free of plating





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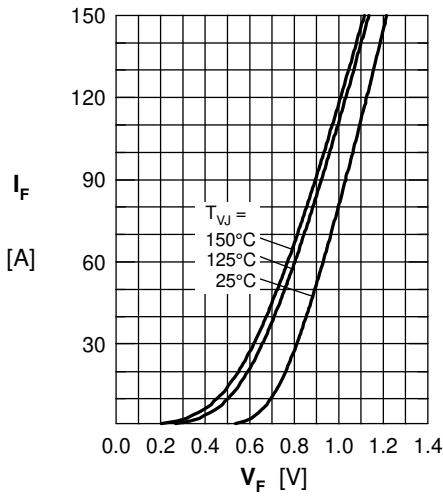


Fig. 1 Maximum forward voltage drop characteristics

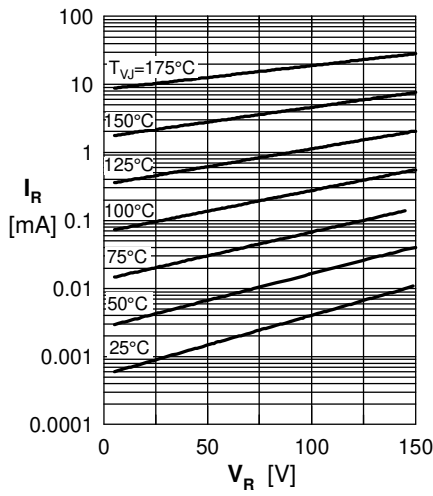


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

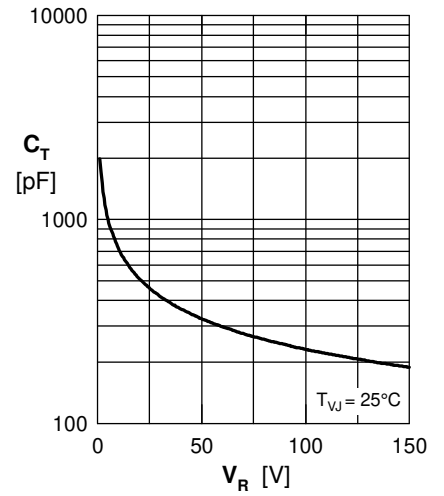


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

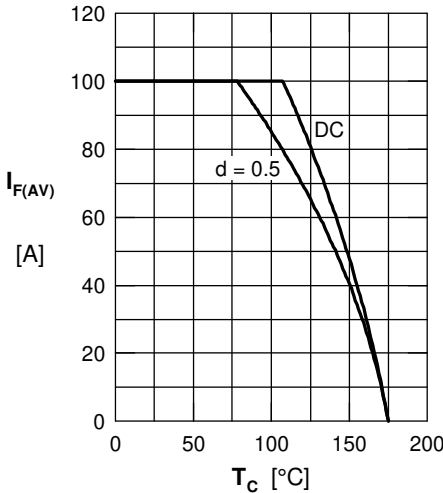


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C

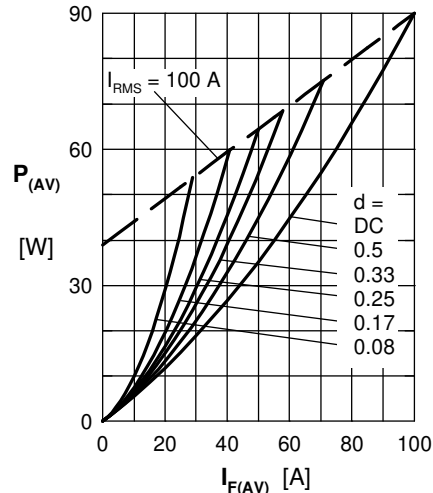


Fig. 5 Forward power loss @ $T_J = 175^\circ\text{C}$

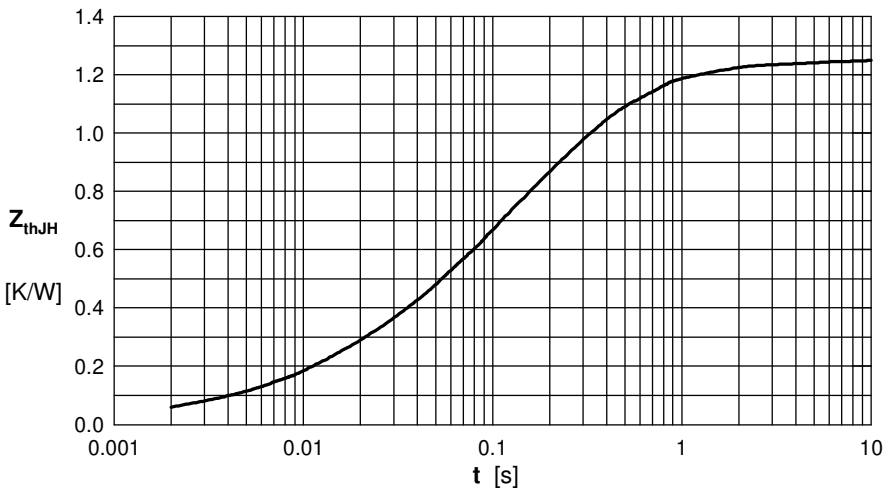


Fig. 6 Transient thermal impedance junction

Note: All curves are per diode